NSN 5962-01-420-4642



Memory Microcircuit - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5962-01-420-4642 **Body Length:** 0.358 inches **Body Width:** 0.358 inches **Body Height:** 0.100 inches **Maximum Power Dissipation Rating:** 500.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** Pacer dawn **Features Provided:** Burn in and electrostatic sensitive and hermetically sealed and programmed and positive outputs and monolithic **Inclosure Material:** Ceramic and glass **Inclosure Configuration:** Leadless flat pack **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Criticality Code Justification:** Cbbl **Case Outline Source And Designator:** C-2 mil-m-38510 **Terminal Surface Treatment:** Solder **Product Name:** Microcircuit, programmed (pal 16r8a) Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source **Time Rating Per Chacteristic:** 25.00 nanoseconds propagation delay time, high to low level output and 25.00 nanoseconds propagation delay time, low to high level

output

Memory Device Type:

Pal

Special Features:

Altered item, made from device p/n 81036082x, cage 67268, microcircuit, memory, programmable logic, monolithic silicon

Test Data Document:

96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal	Type And	Quantity:

20 leadless

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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